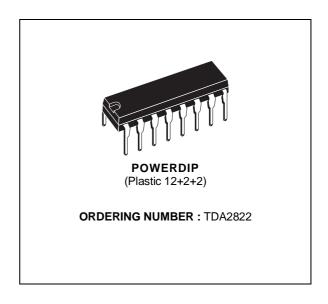




DUAL POWER AMPLIFIER

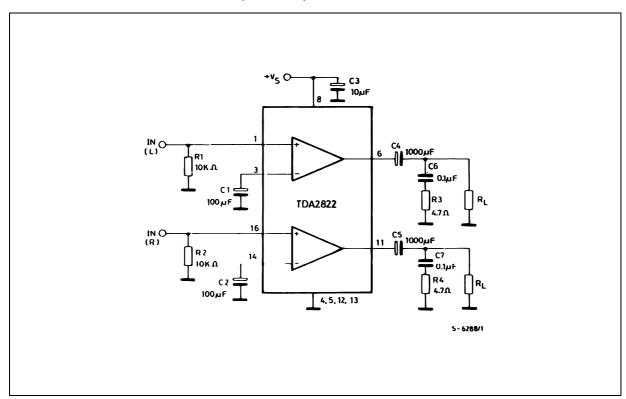
- SUPPLY VOLTAGE DOWN TO 3 V
- LOW CROSSOVER DISTORSION
- LOW QUIESCENT CURRENT
- BRIDGE OR STEREO CONFIGURATION



DESCRIPTION

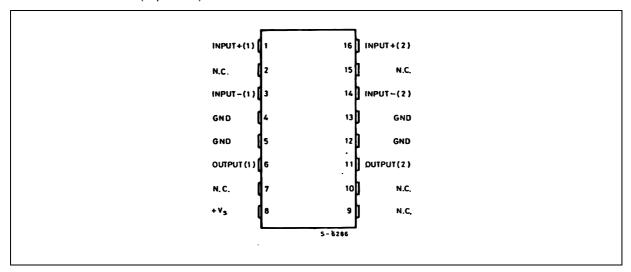
The TDA2822 is a monolithic integrated circuit in 12+2+2 powerdip, intended for use as dual audio power amplifier in portable radios and TS sets.

TYPICAL APPLICATION CIRCUIT (STEREO)

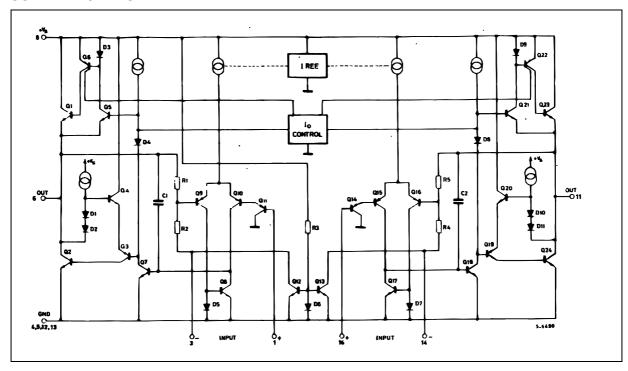


March 1995 1/11

PIN CONNECTION (top view)



SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------------------------------|--|-------------|----------|
| Vs | Supply Voltage | 15 | V |
| Ιο | Output Peak Current | 1.5 | Α |
| | Total Power Dissipation at T_{amb} = 50 °C at T_{case} = 70 °C | 1.25 4 | W W |
| T _{stq} , T _i | Storage and Junction Temperature | - 40 to 150 | °C |



THERMAL DATA

| Symbol | Parameter | Value | Unit |
|------------------------|---|-------|------|
| R _{th i-amb} | Thermal Resistance Junction-ambient Max | 80 | °C/W |
| R _{th j-case} | Thermal Resistance Junction-pins Max | 20 | °C/W |

ELECTRICAL CHARACTERISTICS (Vs = 6 V, $T_{amb} = 25 °C$, unless otherwise specified) STEREO (test circuit of fig. 1)

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Unit |
|----------------|-----------------------------|--|-------------|---------------------|------|-------------|
| V_s | Supply Voltage | | 3 | | 15 | V |
| V _c | Quiescent Output Voltage | $V_s = 9 V$ | | 4 | | V |
| | | V _s = 6 V | | 2.7 | | V |
| I_d | Quiescent Drain Current | | | 6 | 12 | mA |
| l _b | Input Bias Current | | | 100 | | nA |
| Po | Output Power (each channel) | $\begin{array}{lll} d = 10 \; \% & f = 1 \; kHz \\ V_s = 9 \; V & R_L = 4 \; \Omega \\ V_s = 6 \; V & R_L = 4 \; \Omega \\ V_s = 4.5 \; V & R_L = 4 \; \Omega \end{array}$ | 1.3 0.45 | 1.7 0.65 0.32 | | W W W |
| G_v | Closed Loop Voltage Gain | f = 1 kHz | 36 | 39 | 41 | dB |
| Ri | Input Resistance | f = 1 kHz | 100 | | | kΩ |
| ^e N | Total Input Noise | $R_s = 10 \text{ k}\Omega$ B = 22 Hz to 22 kHz Curve A | | 2.5 2 | | μV μV |
| SVR | Supply Voltage Rejection | f = 100 Hz | 24 | 30 | | dB |
| CS | Channel Separation | $R_q = 10 \text{ k}\Omega \text{ f} = 1 \text{ kHz}$ | | 50 | | dB |

BRIDGE (test circuit of fig. 2)

| Vs | Supply Voltage | | 3 | | 15 | V |
|----------------|--------------------------|--|------------|------------------|----|-------------|
| I_d | Quiescent Drain Current | R _L = ∞ | | 6 | 12 | mA |
| Vos | Output Offset Voltage | $R_L = 8 \Omega$ | | 10 | 60 | mV |
| I _b | Input Bias Current | | | 100 | | nA |
| Po | Output Power | $ d = 10 \% f = 1 \text{ kHz} $ $ V_s = 9 \text{ V} R_L = 8 \Omega $ $ V_s = 6 \text{ V} R_L = 8 \Omega $ $ V_s = 4.5 \text{ V} R_L = 4 \Omega $ | 2.7 0.9 | 3.2 1.35 1 | | W W W |
| d | Distortion (f = 1 kHz) | $R_L = 8 \Omega$ $P_o = 0.5 W$ | | 0.2 | | % |
| Gv | Closed Loop Voltage Gain | f = 1 kHz | | 39 | | dB |
| Ri | Input Resistance | f = 1 kHz | 100 | | | kΩ |
| ^e N | Total Input Noise | $R_s = 10 \text{ k}\Omega$ B = 22 Hz to 22 kHz Curve A | | 3 2.5 | | μV μV |
| SVR | Supply Voltage Rejection | f = 100 Hz | | 40 | | dB |

Figure 1: Test Circuit (stereo).

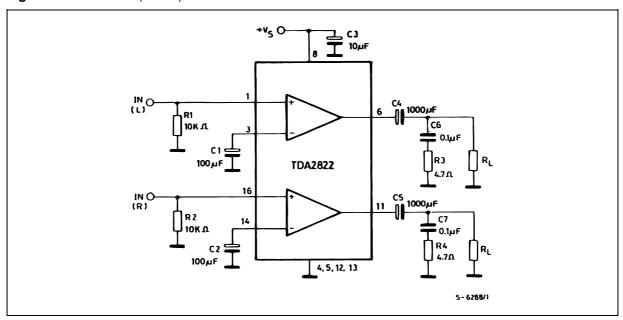


Figure 2: P.C. Board and Components Layout of the Circuit of Figure 1 (1:1 scale).

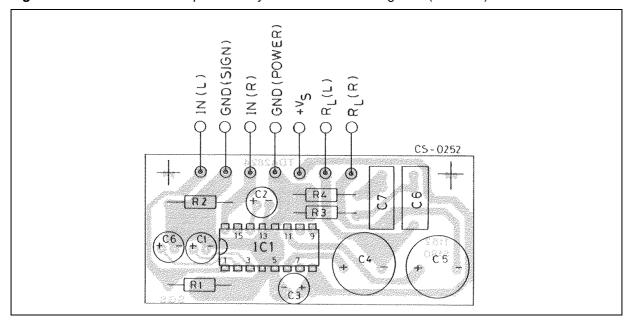


Figure 3 : Test Circuit (bridge).

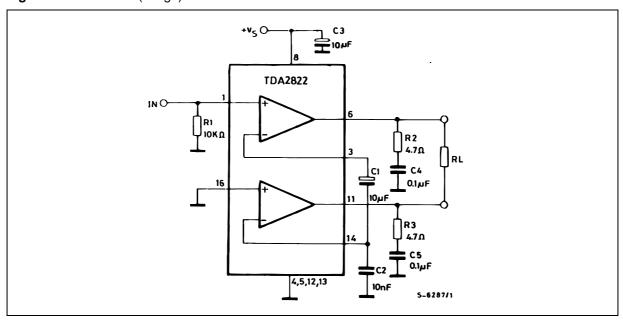


Figure 4: P.C. Board and Components Layout of the Circuit of Figure 3 (1:1 scale).

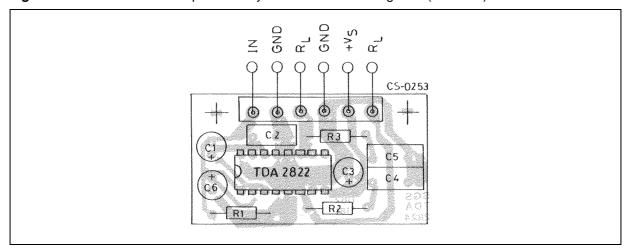


Figure 5 : Output Power vs. Supply Voltage (Stereo).

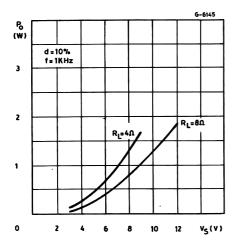


Figure 7: Distorsion vs. Output Power (Bridge).

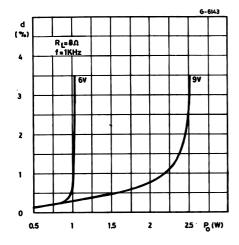


Figure 9 : Supply Voltage Rejection vs. Frequency.

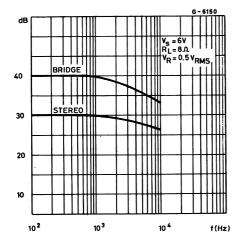


Figure 6 : Output Power vs. Supply Voltage (Bridge).

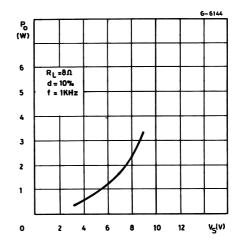


Figure 8: Distorsion vs. Output Power (Bridge).

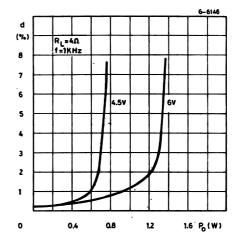


Figure 10 : Quiescent Current vs. Supply Voltage.

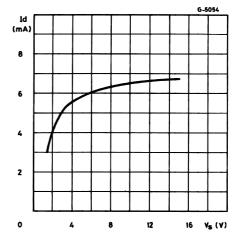


Figure 11 : Total Power Dissipation vs. Output Power (Stereo).

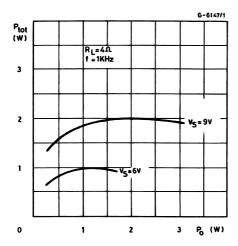


Figure 13 : Total Power Dissipation vs. Output Power (Bridge).

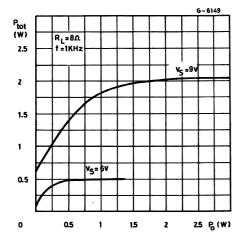


Figure 12 : Total Power Dissipation vs. Output Power (Bridge).

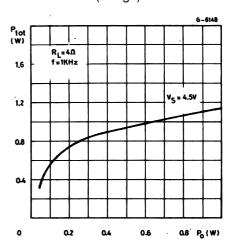
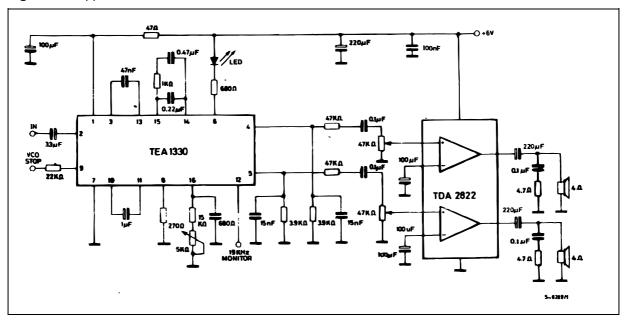


Figure 14: Application Circuit for Portable Radios.

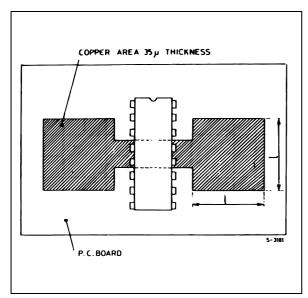


MOUNTING INSTRUCTION

The R_{th j-amb} of the TDA2822 can be reduced by soldering the GND pins to a suitable copper area of the printed circuit board (Figure 15) or to an external heatsink (Figure 16).

The diagram of Figure 17 shows the maximum dissipable power P_{tot} and the $R_{th\ j\text{-}amb}$ as a function of the side " ∂ " of two equal square copper areas having a thickness of 35 μ (1.4 mils).

Figure 15 : Example of P.C. Board Copper Area which is used as Heatsink.



During soldering the pins temperature must not exceed 260 °C and the soldering time must not be longer than 12 seconds.

The external heatsink or printed circuit copper area must be connected to electrical ground.

Figure 16 : External Heatsink Mounting Example.

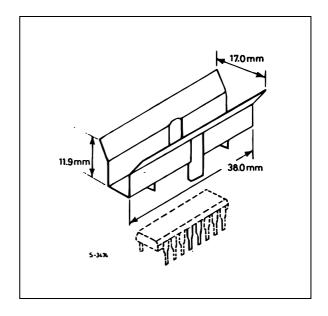


Figure 6 : Maximum Dissipable Power and Junction to Ambient Thermal Resistance vs. Side "\u00f3".

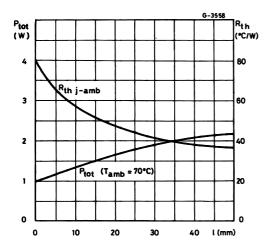
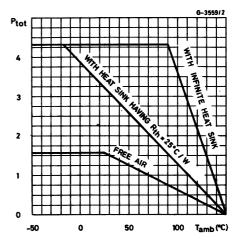
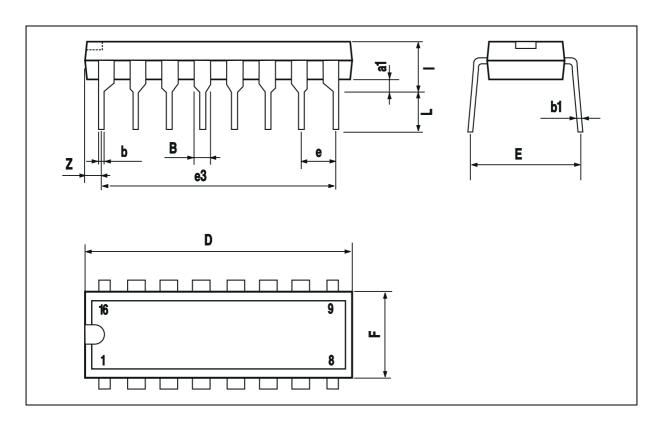


Figure 7 : Maximum Allowable Power Dissipation vs. Ambient Temperature.



POWERDIP 16 PACKAGE MECHANICAL DATA

| DIM. | mm | | | inch | | | |
|-------|------|-------|------|-------|-------|-------|--|
| Dini. | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. | |
| a1 | 0.51 | | | 0.020 | | | |
| В | 0.85 | | 1.40 | 0.033 | | 0.055 | |
| b | | 0.50 | | | 0.020 | | |
| b1 | 0.38 | | 0.50 | 0.015 | | 0.020 | |
| D | | | 20.0 | | | 0.787 | |
| E | | 8.80 | | | 0.346 | | |
| е | | 2.54 | | | 0.100 | | |
| e3 | | 17.78 | | | 0.700 | | |
| F | | | 7.10 | | | 0.280 | |
| I | | | 5.10 | | | 0.201 | |
| L | | 3.30 | | | 0.130 | | |
| Z | | | 1.27 | | | 0.050 | |



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